

Schottky Barrier Diode

■ Applications

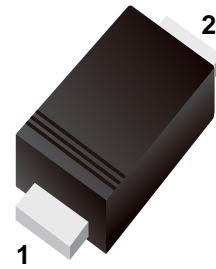
General rectification

■ Features

- 1) Small power mold type. (PMDS)
- 2) Low I_R .
- 3) High reliability.

■ Construction

Silicon epitaxial planar

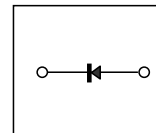


■ Simplified outline(SOD-123FL)

■ Marking

Marking	74
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■ Structure



■ Absolute maximum ratings (Ta=25°C)

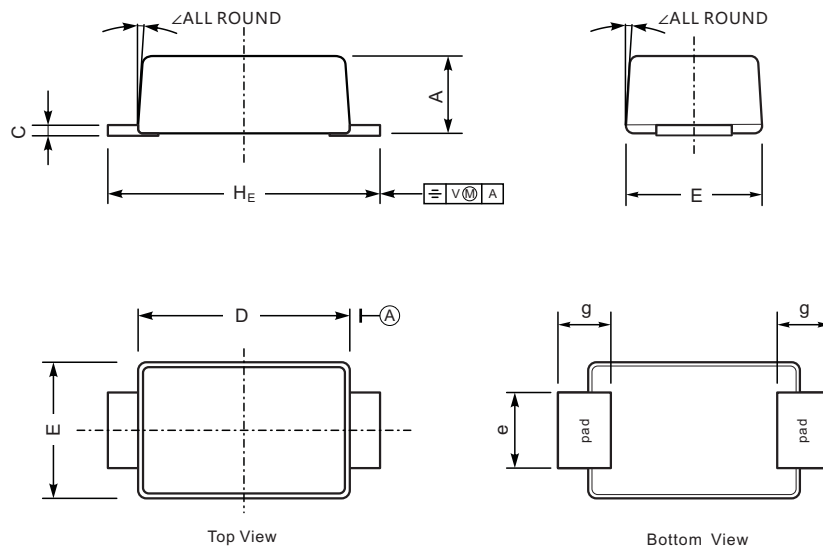
Parameter	Symbol	Limits	Unit
Reverse voltage (repetitive peak)	V_{RM}	40	V
Reverse voltage (DC)	V_R	40	V
Average rectified forward current	I_o	1	A
Forward current surge peak (60Hz·1cyc)	I_{FSM}	30	A
Junction temperature	T_j	150	°C
Storage temperature	T_{stg}	-40 to +150	°C

(*1) Mounted on epoxy board. 180°Half sine wave

■ Electrical characteristics (Ta=25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Forward voltage	V_F	-	0.46	0.51	V	$I_F=1.0A$
Reverse current	I_R	-	4.0	30	μA	$V_R=40V$

■ SOD-123FL



UNIT		A	C	D	E	e	g	H_E	\angle
mm	max	1.1	0.20	2.9	1.9	1.1	0.9	3.8	7°
	min	0.9	0.12	2.6	1.7	0.8	0.7	3.5	
mil	max	43	7.9	114	75	43	35	150	
	min	35	4.7	102	67	31	28	138	